
Design of Power Electronics Reliability:

A New, Interdisciplinary Approach

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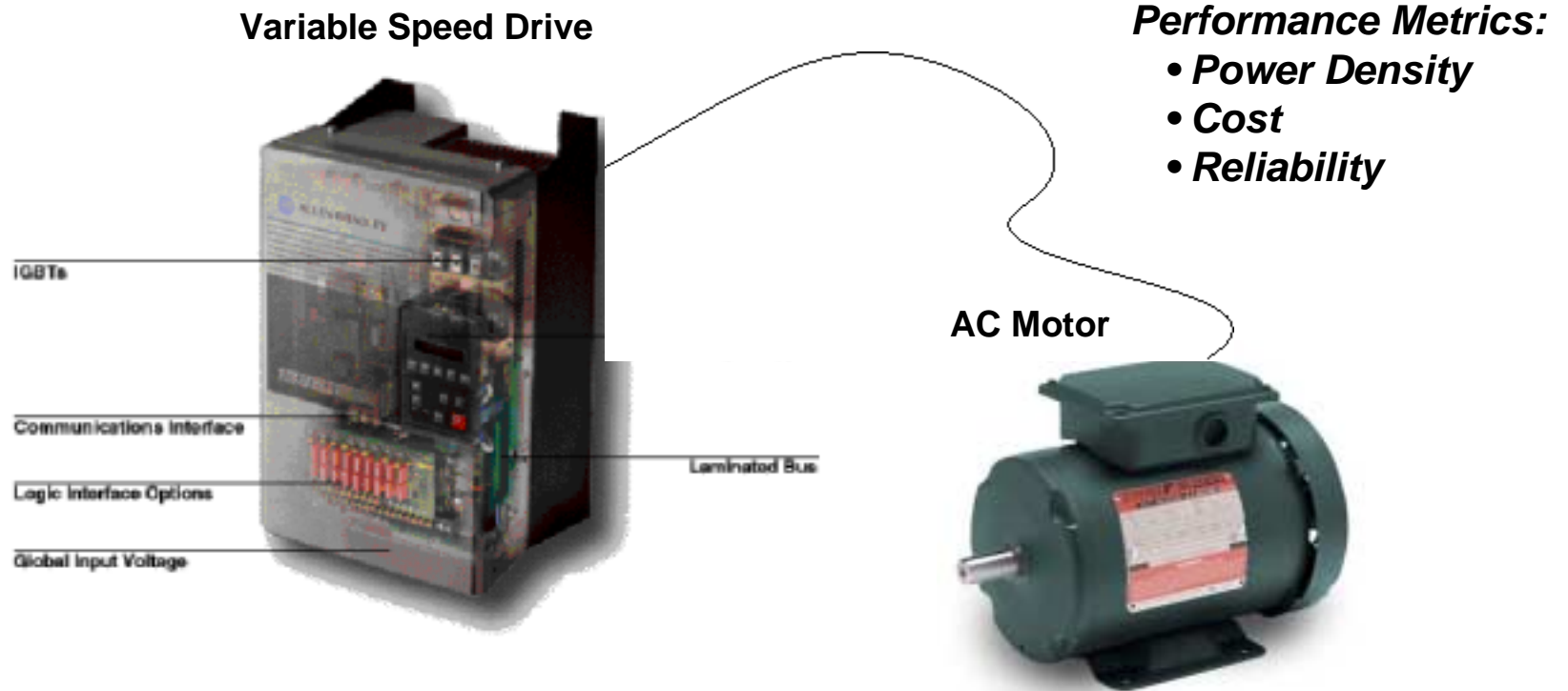
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**Mr. Bruce Beihoff,
*Manager, Solid State Power Assembly Laboratory, RA***

Variable Speed Drive & Motor Automation System

Overview - MCS 3



Converts AC power (fixed frequency, voltage) to
AC Power (variable frequency, current, and voltage)

Enables exact control of speed (RPM) and torque of *motors*

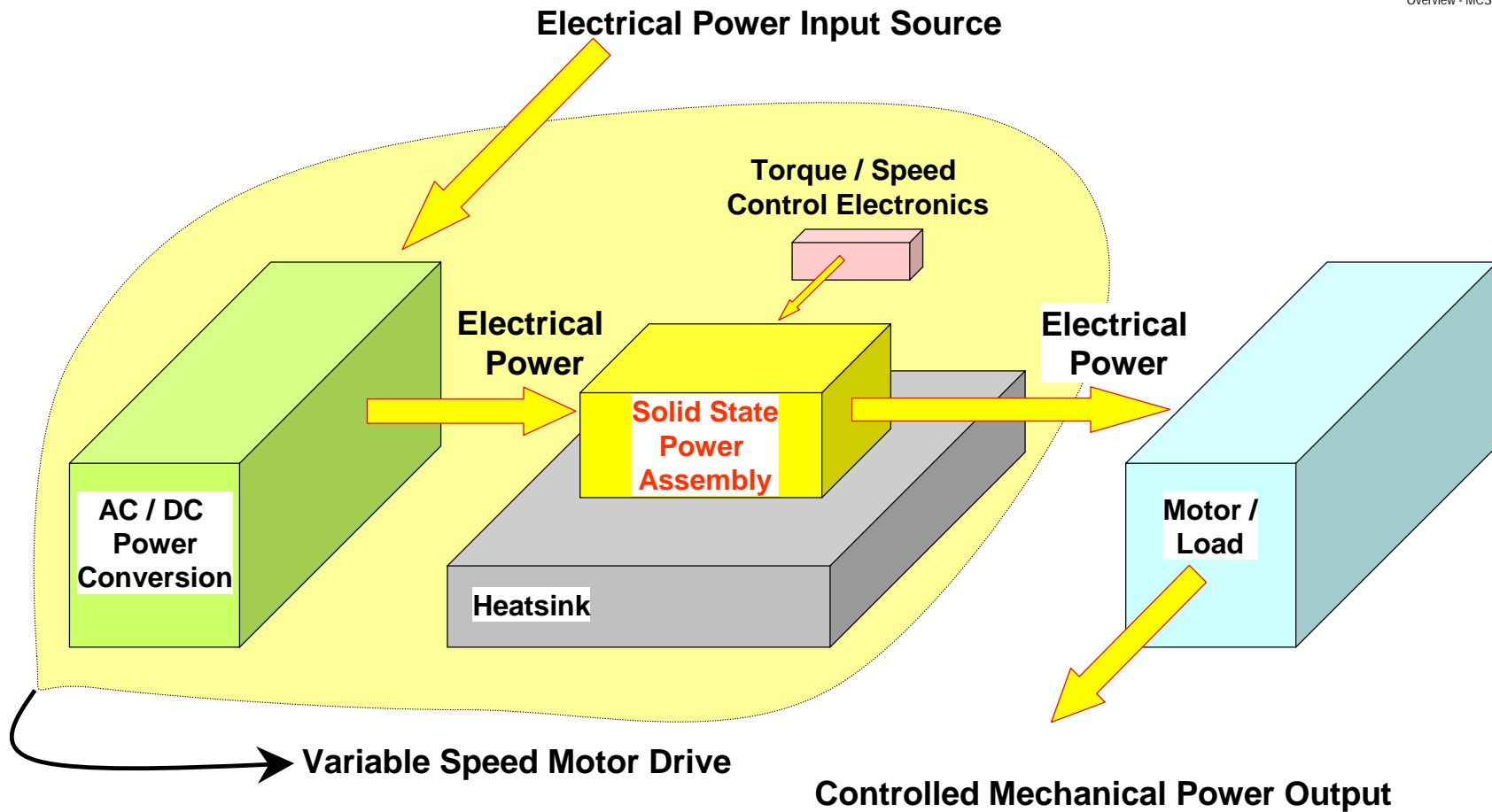
Motors become controlled electromechanical energy converters.

Variable Speed Drive and Motor Applications

Overview - MCS 4

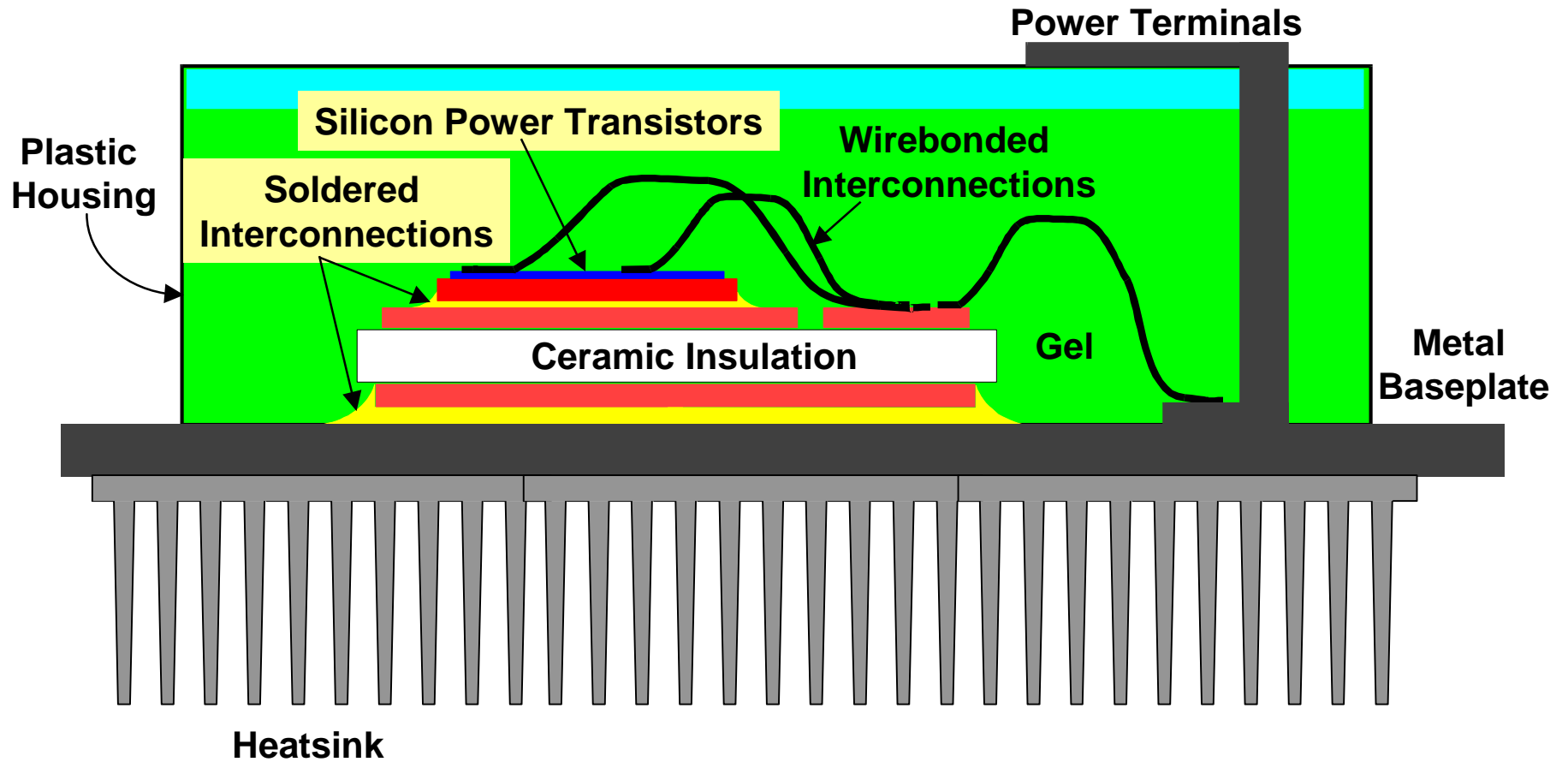
- **Factory assembly lines**
- **Heating, ventilation and air-conditioning**
- **Refrigeration**
- **Disc drives / digital storage**
- **Electric / hybrid vehicles - commercial and military**
- **Rail transport**
- **Elevators**
- **Actuation of e.g., military aircraft controls, ship controls**
- ***Practically anything that moves!***

Variable Speed Motor Drive Block Diagram



The “Heart” of the Motor Drive: *The Solid-State Power Assembly*

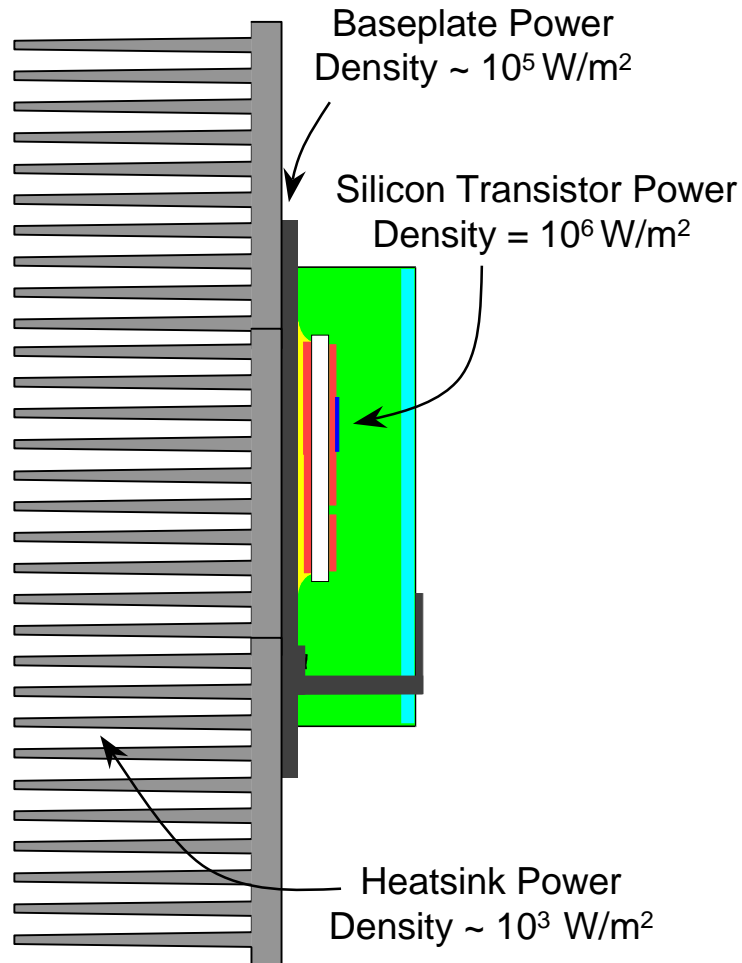
Overview - MCS 6



Schematic Cross Section of Typical Solid State Power Assembly

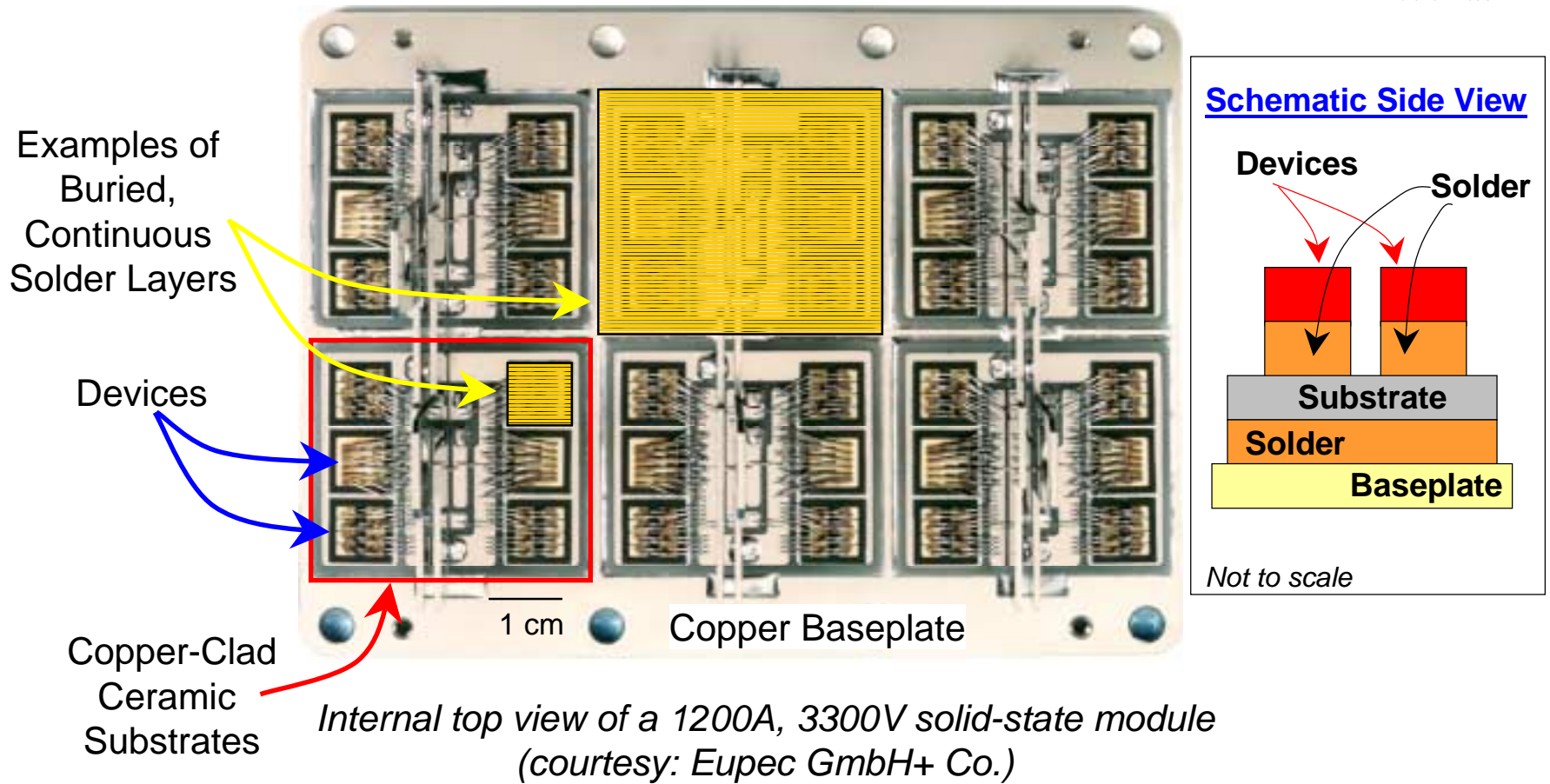
Thermal Management Goal: Decrease Power Density Between Device & Heatsink

Overview - MCS 7



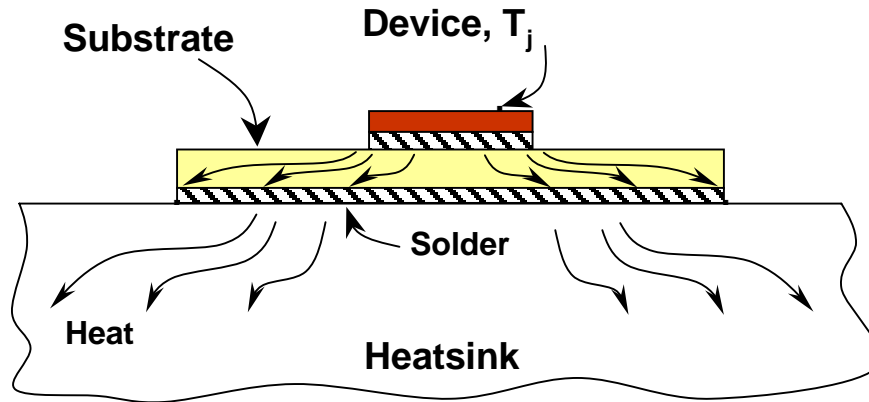
Thin, Large Area Solder Joints Unique to Solid-State Power Assemblies

Overview - MCS 8



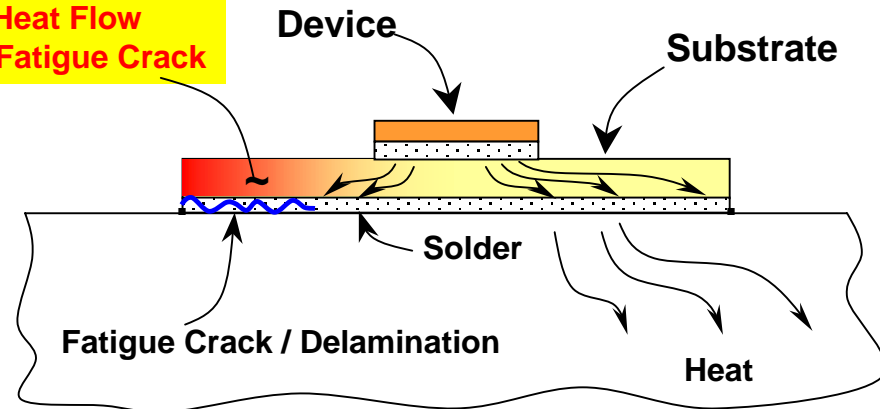
Solder Joint Cracking/Delamination Raises Package Thermal Resistance

Pristine condition

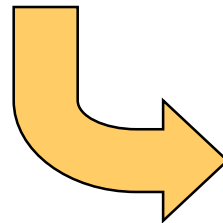


Damaged condition

No Heat Flow
b/c Fatigue Crack



After Some Period
of Operation



Driving Force for Delamination: Mechanical Strain Energy Release Rate, G_I

Overview - MCS 10

$$\frac{Z \sigma^2 h (1 - \nu^2)}{E} = G_I$$

$Z \sim 0.3$ for this geometry

E = Young's modulus

ν = Poisson's ratio

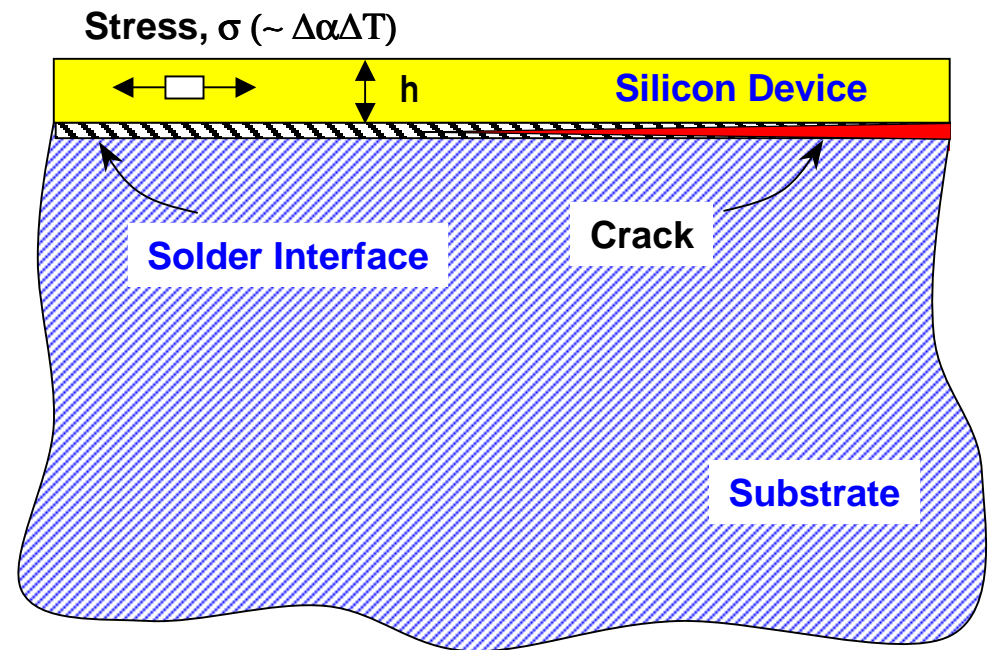
σ = In-plane mechanical stress

h = Top layer thickness

G_I = Applied strain energy release rate

$\Delta\alpha$ = Coefficient of thermal expansion mismatch

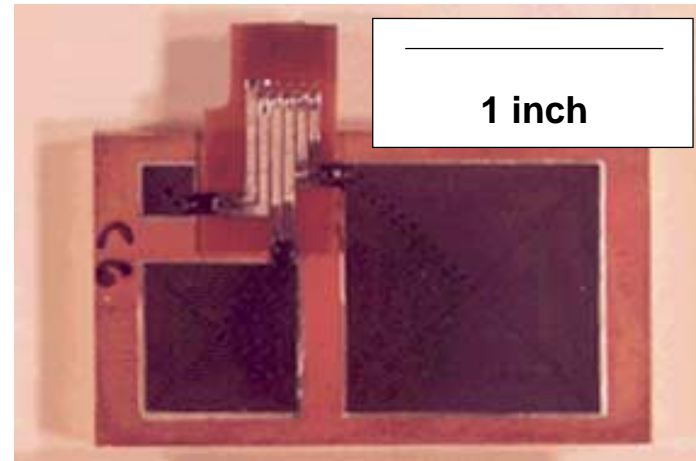
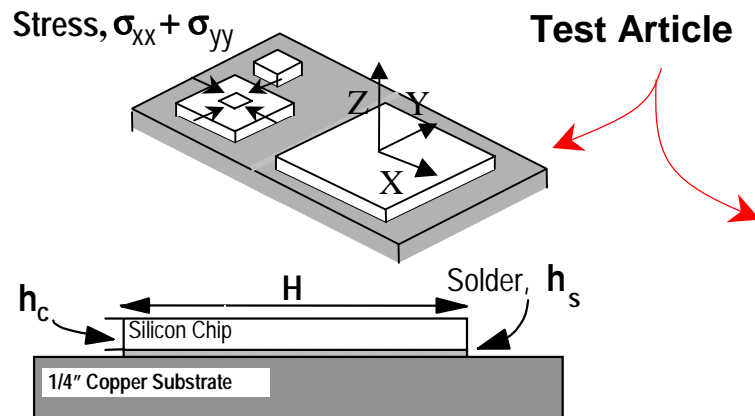
ΔT = Range of temperature excursion



***Mechanical strain energy release rate, G_I ,
is the “applied load”***

Experimental Methodology: *Materials and Architectures*

Overview - MCS 11



Three silicon device sizes:

Small: 0.2" square
Medium: 0.6" square
Large: 1.0" square

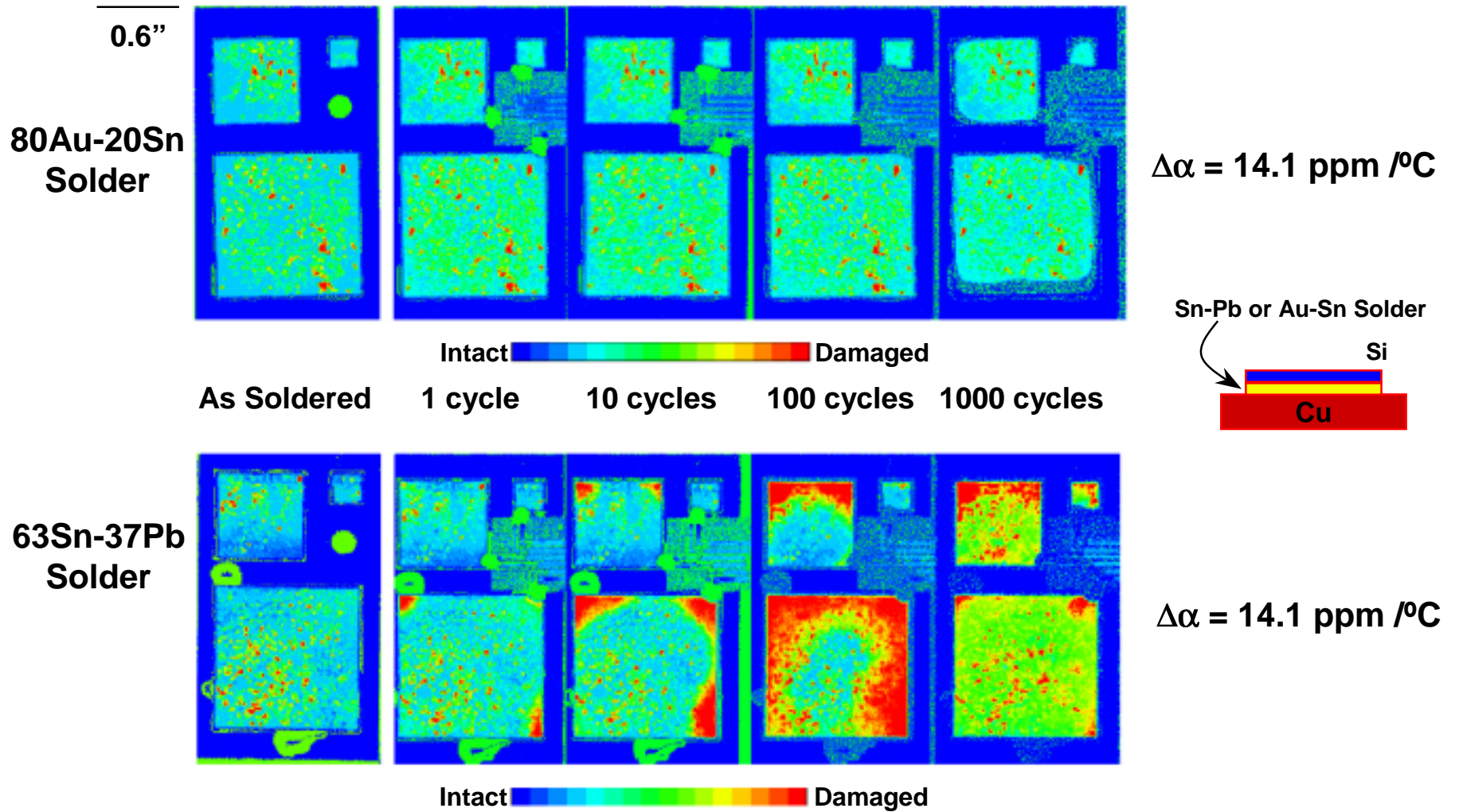
Four solder compositions:

97.5Pb/1.5Ag/1.0Sn ($T_m=309^\circ\text{C}$)
80Au/20Sn ($T_m=280^\circ\text{C}$)
96.5Sn/3.5Ag ($T_m=221^\circ\text{C}$)
63Sn/37Pb ($T_m=183^\circ\text{C}$)

Three substrate coefficients of thermal expansion (CTE)

Low: Kovar (~ 6 ppm/ $^\circ\text{C}$)
Medium: mild steel (~ 12 ppm/ $^\circ\text{C}$)
High: copper (~ 17 ppm/ $^\circ\text{C}$)

Different Solders Exhibit Large Differences in Delamination



Ultrasonic Acoustic Micrographs

Recall: Driving Force for Delamination, G_I

Overview - MCS 13

$$\frac{Z \sigma^2 h (1 - \nu^2)}{E} = G_I$$

$Z \sim 0.3$ for this geometry

E = Young's modulus

ν = Poisson's ratio

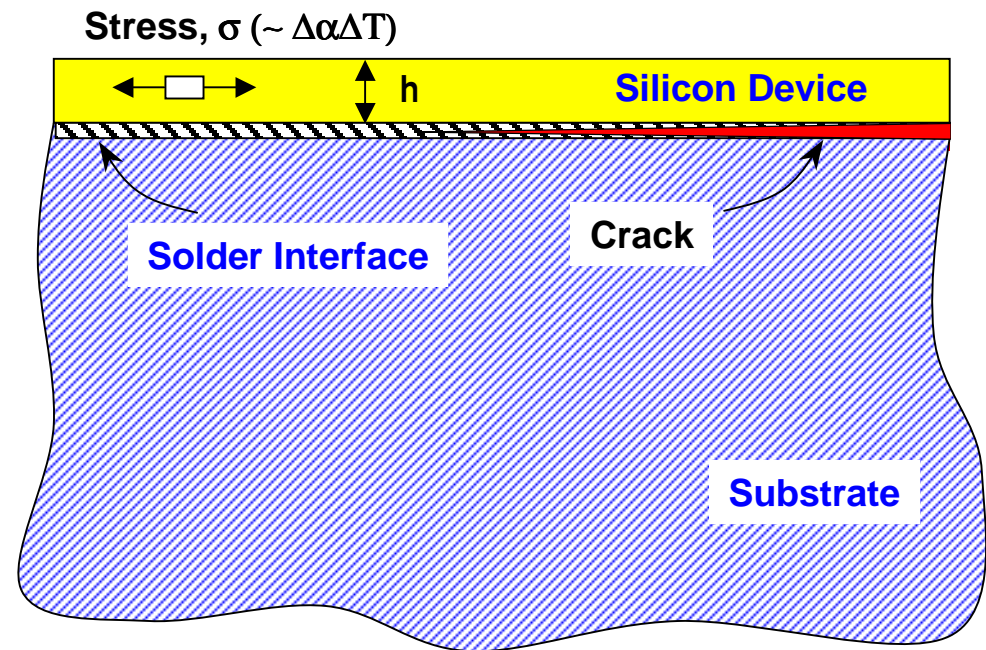
σ = In-plane mechanical stress

h = Top layer thickness

G_I = Applied strain energy release rate

$\Delta\alpha$ = Coefficient of thermal expansion mismatch

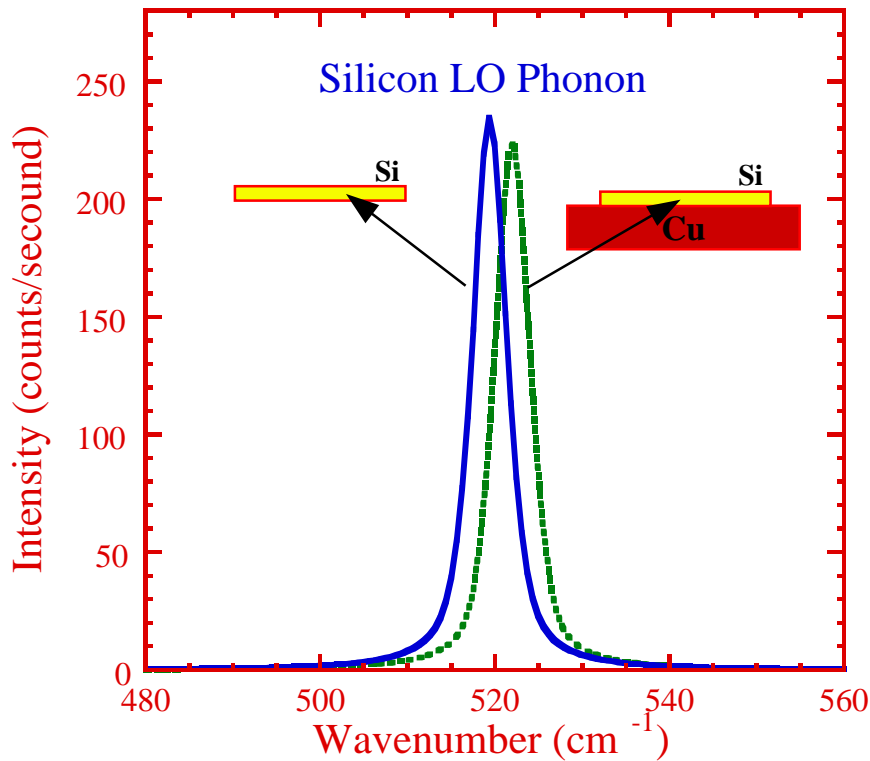
ΔT = Range of temperature excursion



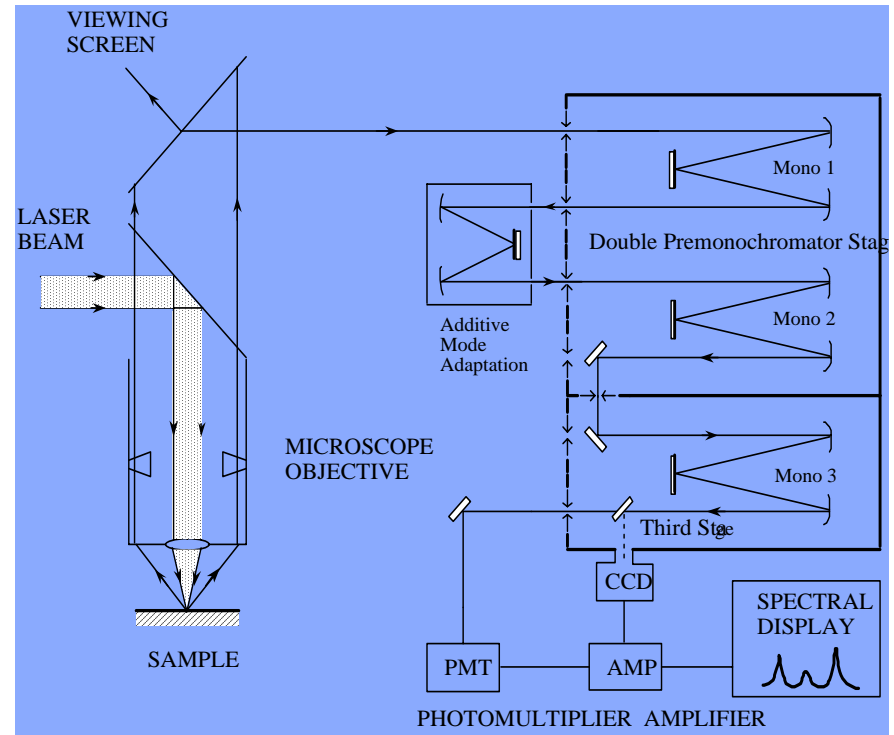
Greater Damage Suggests Higher Stress and Higher G_I ,.....Right?

Piezospectroscopy: Stress Mapping through Raman Spectroscopy

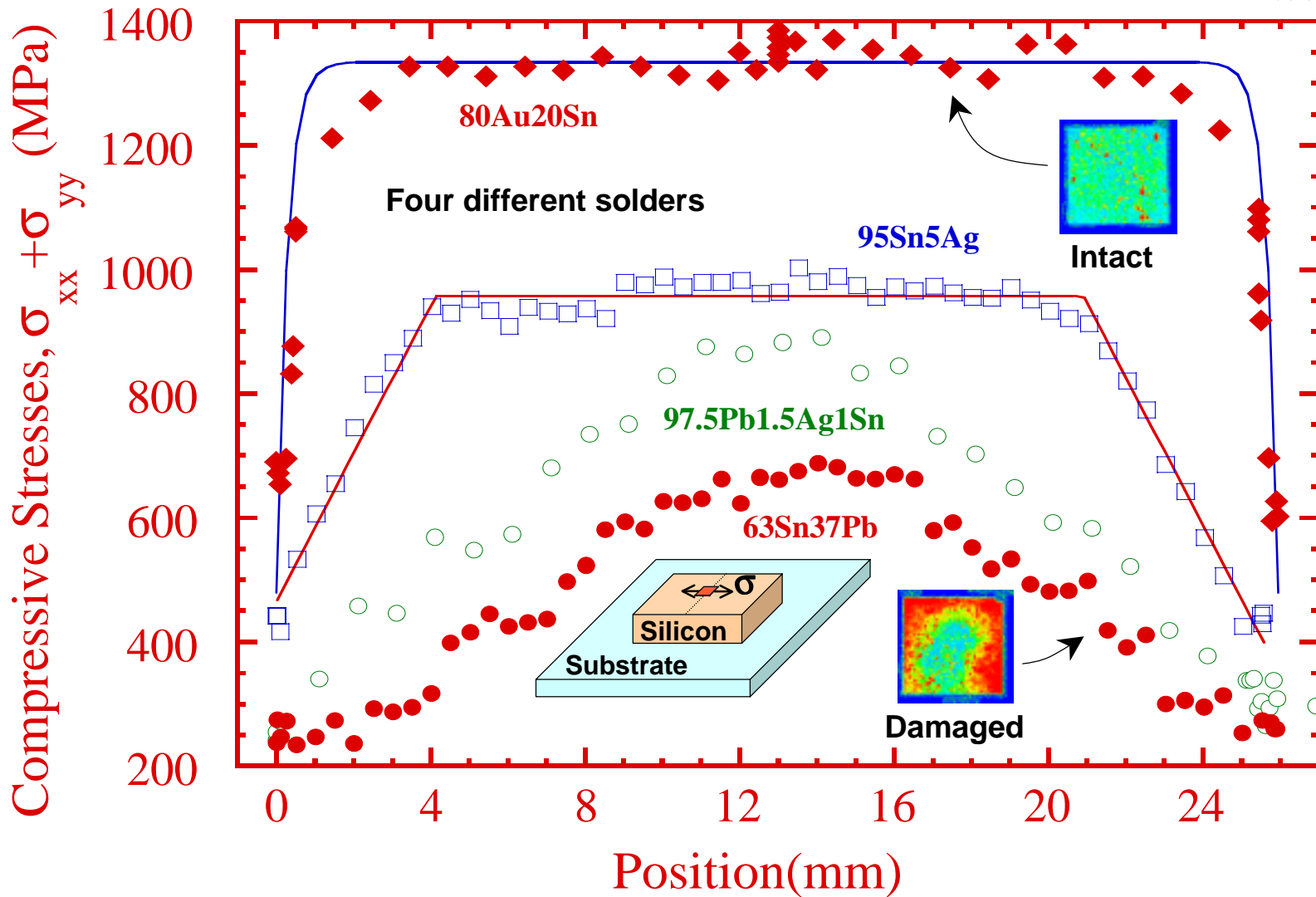
- Stress-Sensitive Raman Peaks



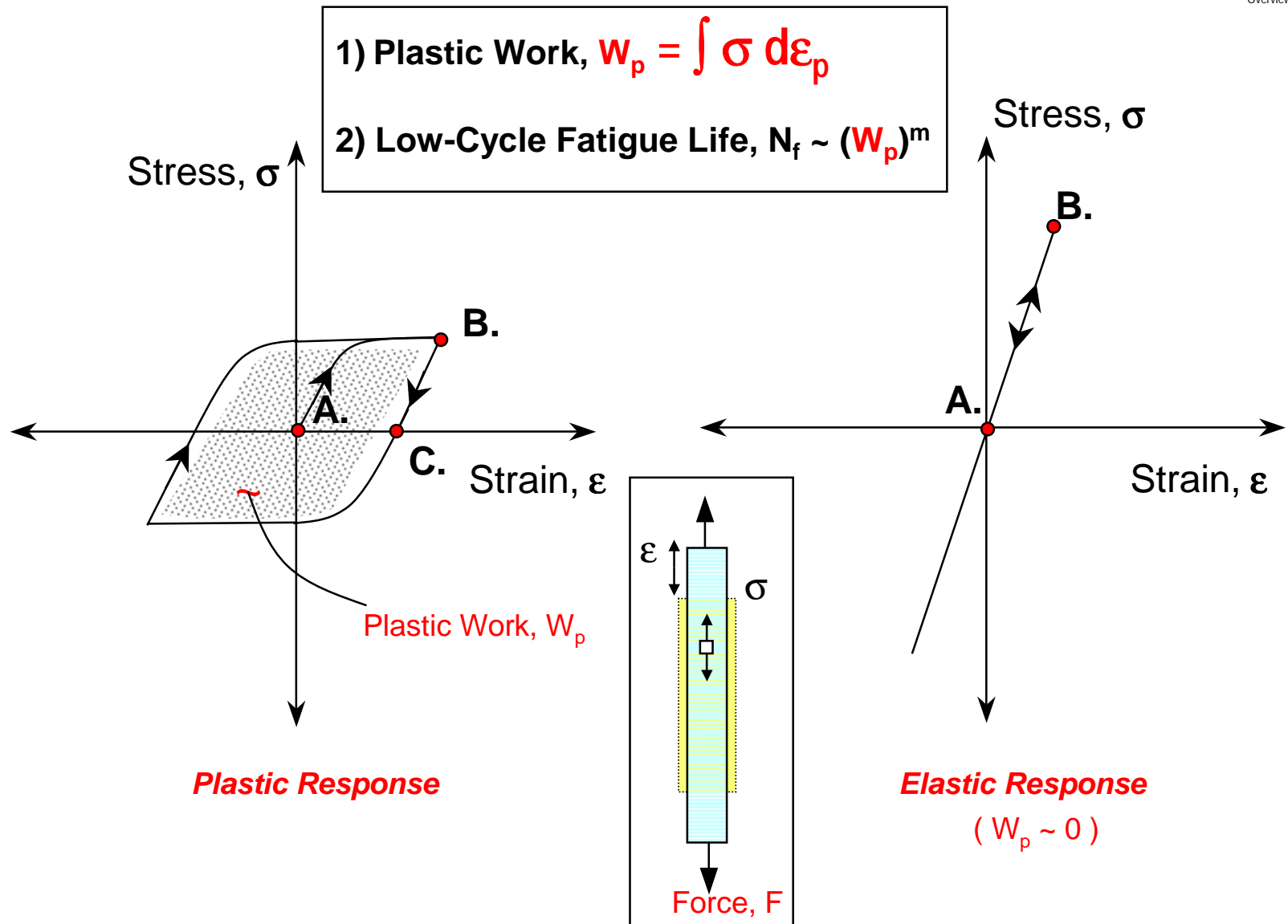
- Raman Probe Optical Path



Solder Damage Depends on *both Stress and Material Resistance*



Material Resistance, G_{Ic} , Depends on Degree of Cyclic Plastic Work, W_p

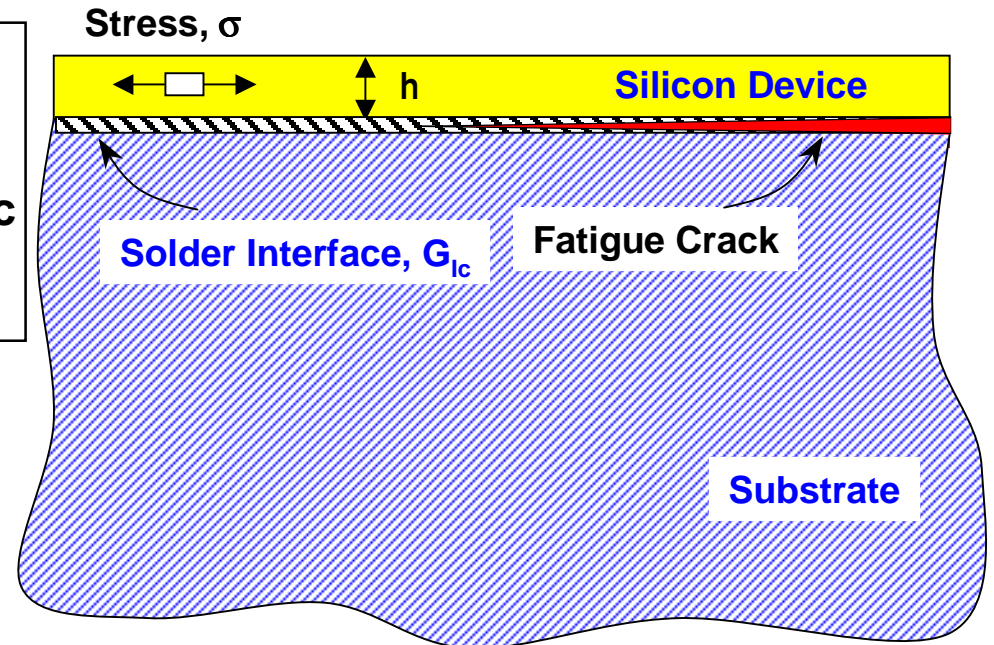


Delamination Only Occurs if G_I is Greater than G_{Ic}

Overview - MCS 17

$$\frac{Z \sigma^2 h (1 - \nu^2)}{E} = G_I \text{ vs. } G_{Ic}$$

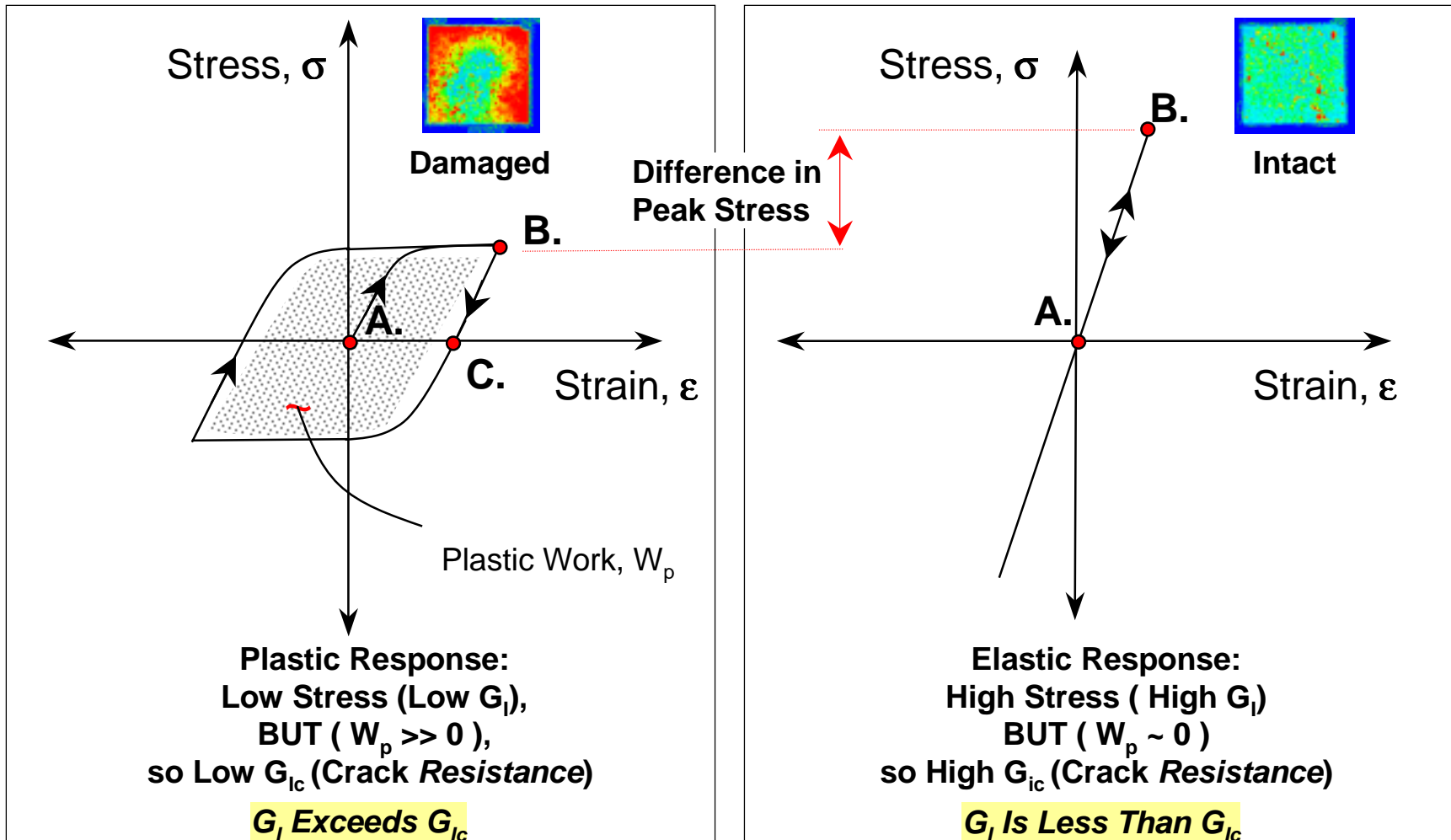
- $Z \sim 0.3$ for this geometry
- E = Young's modulus
- ν = Poisson's ratio
- σ = In-plane mechanical stress
- h = Top layer thickness
- G_{Ic} = Critical G_I for fracture



G_{Ic} is Intrinsic Material Property - G_I is Applied Load

Thus, Fatigue Life Depends on Response of Solder Material as Compared to G_I

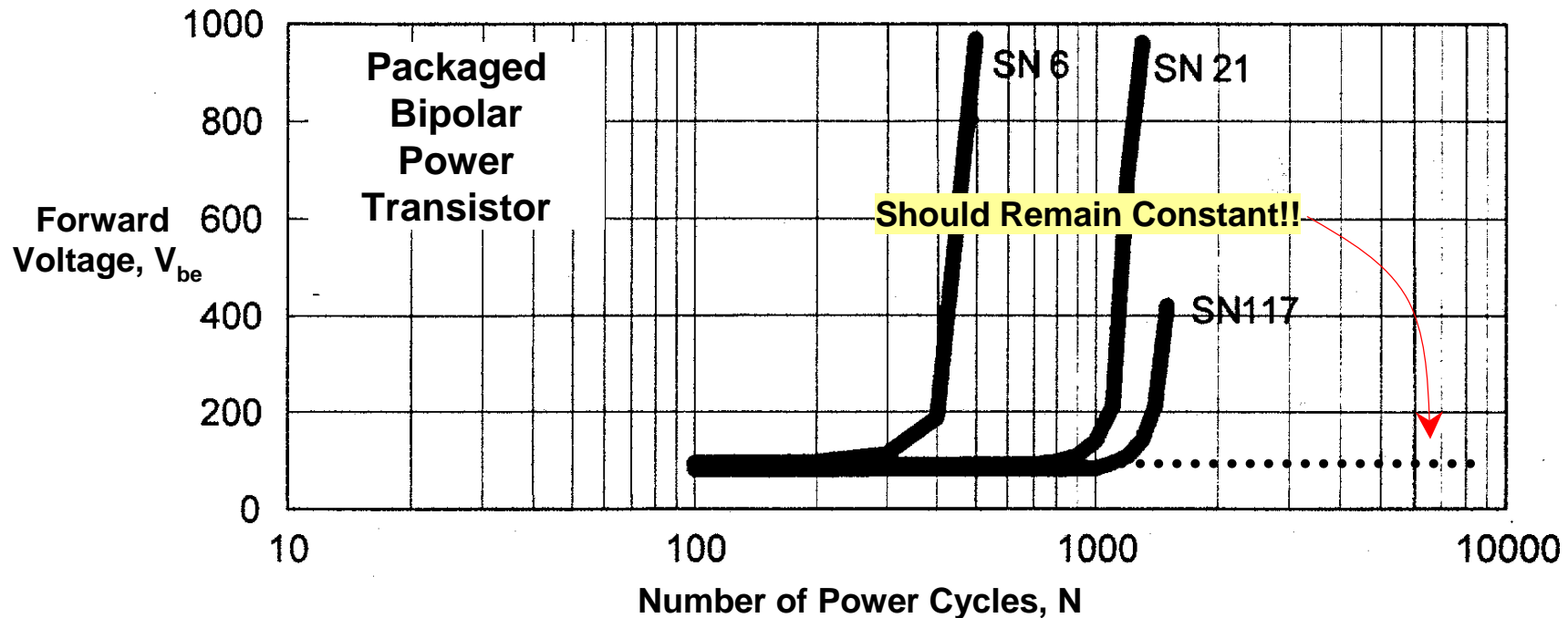
Different Physical Damage Mechanisms Operate in Different Solders!



Back to Our Problem: *Unpredictable Performance Changes!*

Overview - MCS 19

Large Electrical Deviations May Occur During Operation



Now we can apply our detailed knowledge of thermomechanical stress and response of solder

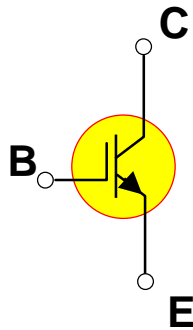
Predicted Electronic Parameter Shift Correlates with Experimental Data

2N3773 npn bipolar

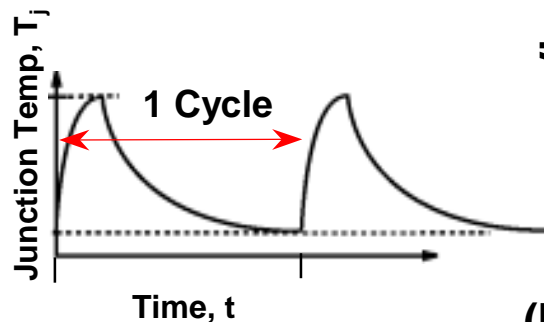
$I_C = 1.5 \text{ A}$

$V_{CE} = 100 \text{ V}$

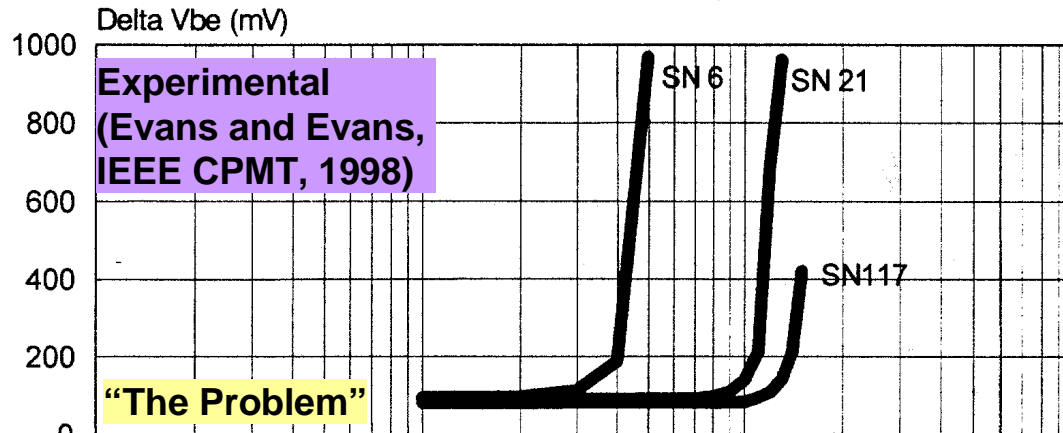
$P_D = 150 \text{ W}$



Bipolar Transistor

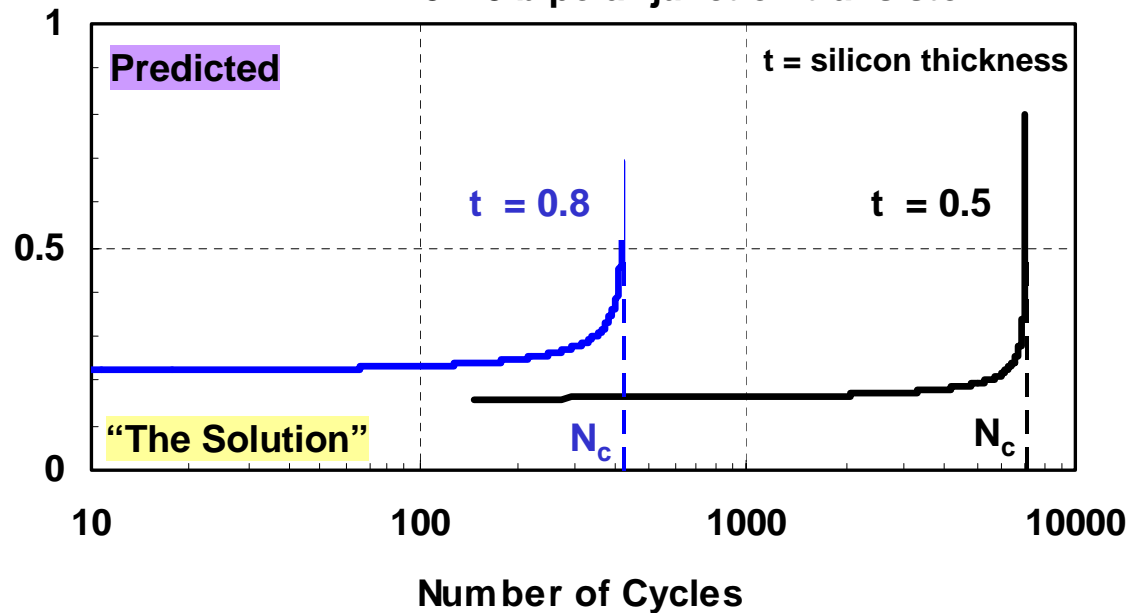


Change in base-emitter
(a) voltage (δV_{be})



2N3773 bipolar junction transistor

(b)



Conclusions

- **Power Electronics Packaging Demands Highly Interdisciplinary Analyses, Experiments & Knowledge**
- **New Methodology Developed to Quantitatively Assess Device/Circuit/System Interactions Resulting from Degradation**
- **Rigorous, Physics-Based Coupling of Electronics / Mechanics / Materials / Heat Transfer**
- **Interfaces are Crucial**
- **Expanding Approach to Explore Biomechanics, Biomaterials Applications and Interactions**